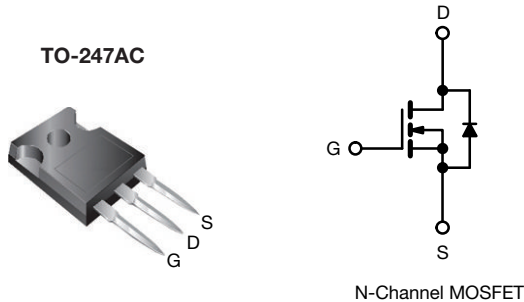


## E Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	700
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V   0.063
$Q_g$ max. (nC)	278
$Q_{gs}$ (nC)	46
$Q_{gd}$ (nC)	76
Configuration	Single



### FEATURES

- Fast body diode MOSFET using E series technology
- Reduced  $t_{rr}$ ,  $Q_{rr}$ , and  $I_{RRM}$
- Low figure-of-merit (FOM):  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Low switching losses due to reduced  $Q_{rr}$
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High intensity discharge (HID)
  - Light emitting diodes (LEDs)
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers
- Renewable energy
  - Solar (PV inverters)
- Switch mode power supplies (SMPS)
  - LLC
  - Phase shifted bridge (ZVS)
  - 3-level inverter
  - AC/DC bridge

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-Free and Halogen-Free	SiHG44N65EF-GE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	46
		$T_C = 100$ °C	29
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	154	A
Linear Derating Factor		3.3	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	596	mJ
Maximum Power Dissipation	$P_D$	417	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125$ °C	70
Reverse Diode $dV/dt$ <sup>d</sup>		5.3	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 6.5$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.



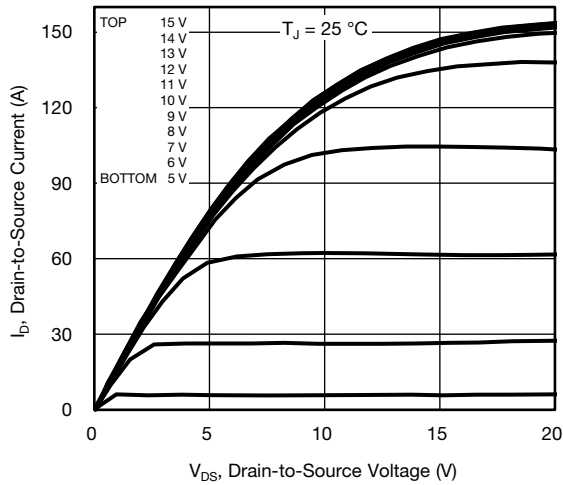
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.3	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 10\text{ mA}$	-	0.75	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 22\text{ A}$	-	0.063	0.073	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 22\text{ A}$	-	17	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	5892	-	pF
Output Capacitance	$C_{oss}$		-	244	-	
Reverse Transfer Capacitance	$C_{rss}$		-	4	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 520\text{ V}$	-	739	-	pF
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$		-	178	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 22\text{ A}, V_{DS} = 520\text{ V}$	-	185	278	nC
Gate-Source Charge	$Q_{gs}$		-	46	-	
Gate-Drain Charge	$Q_{gd}$		-	76	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 22\text{ A}, R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$	-	46	92	ns
Rise Time	$t_r$		-	77	116	
Turn-Off Delay Time	$t_{d(off)}$		-	157	236	
Fall Time	$t_f$		-	100	150	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$	0.2	0.5	1.0	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	46	A
Pulsed Diode Forward Current	$I_{SM}$		-	-	154	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 22\text{ A}, V_{GS} = 0\text{ V}$	-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 22\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$	-	202	404	ns
Reverse Recovery Charge	$Q_{rr}$		-	1.5	3.0	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$		-	14	-	A

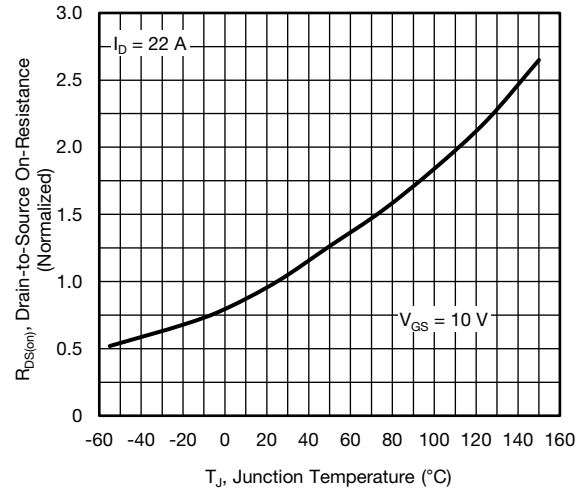
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

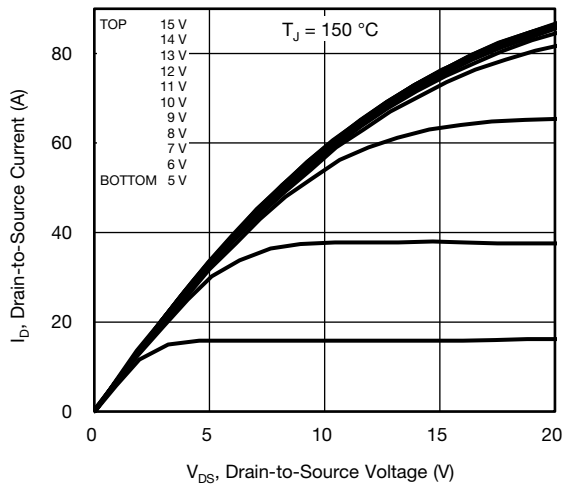
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



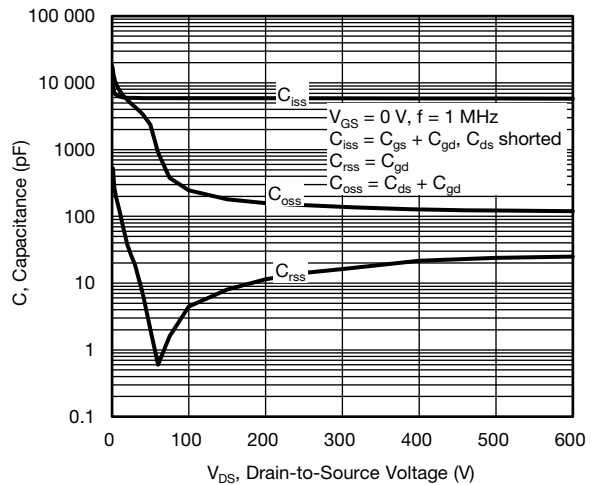
**Fig. 1 - Typical Output Characteristics**



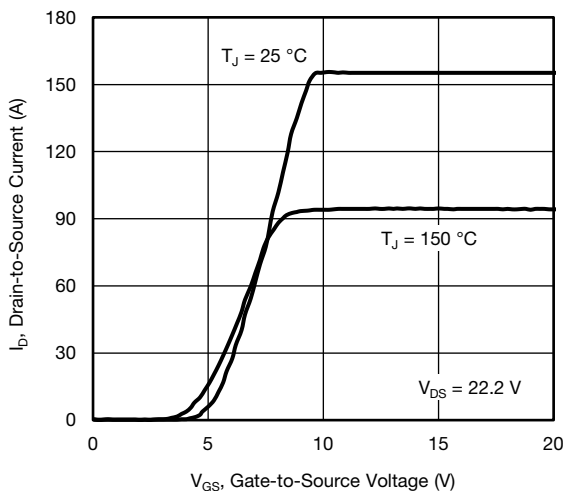
**Fig. 4 - Normalized On-Resistance vs. Temperature**



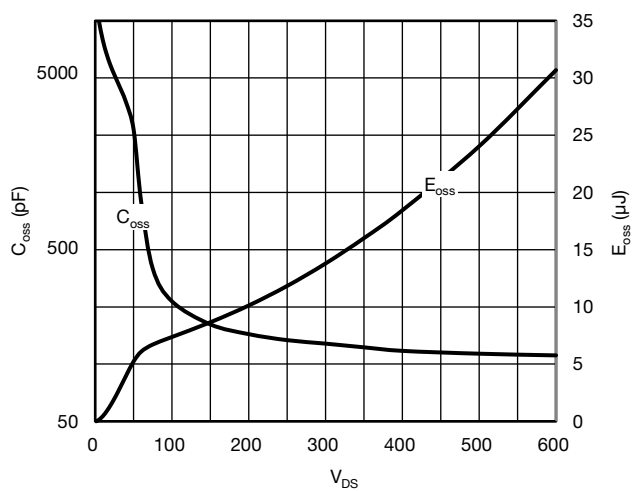
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**

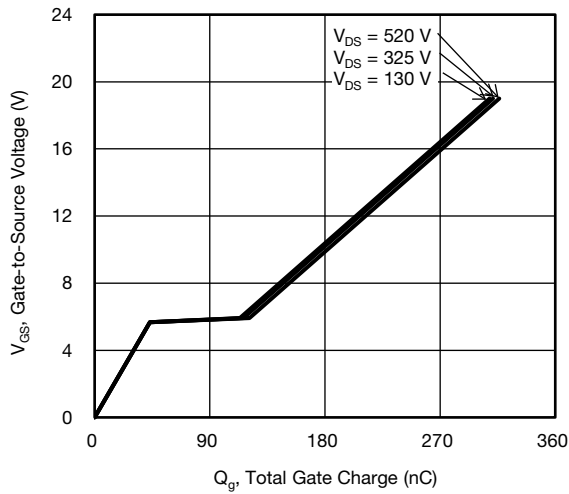


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

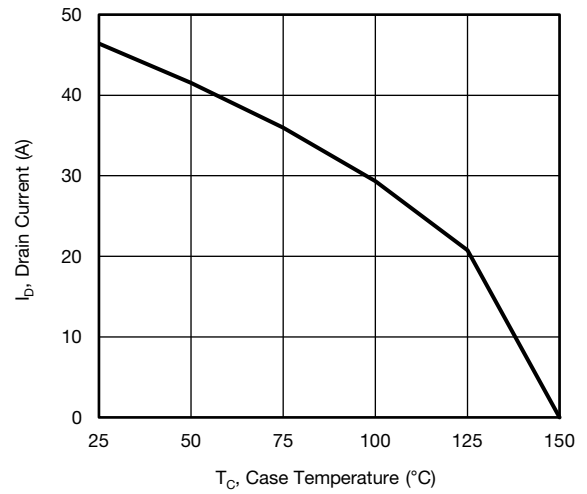


Fig. 10 - Maximum Drain Current vs. Case Temperature

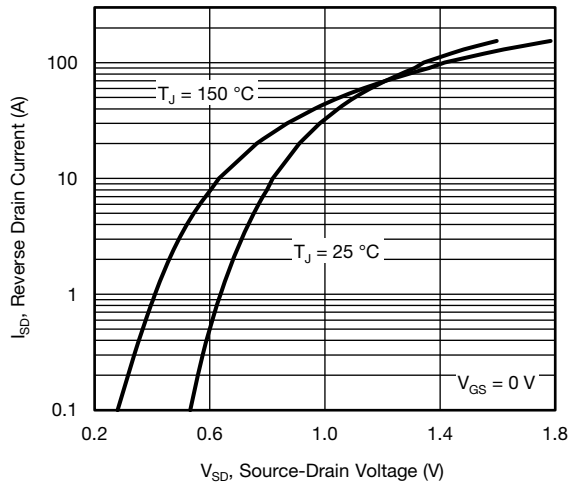


Fig. 8 - Typical Source-Drain Diode Forward Voltage

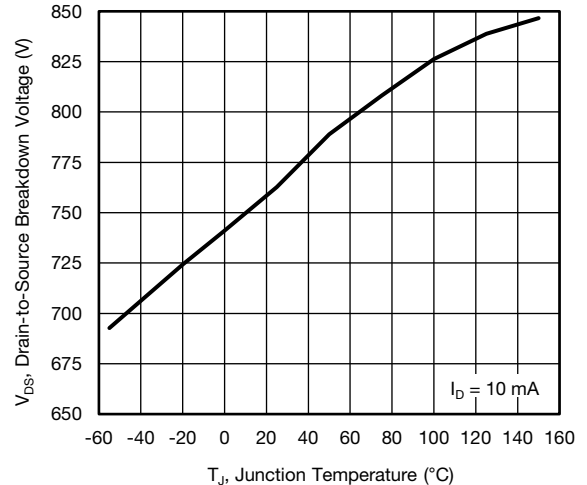


Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

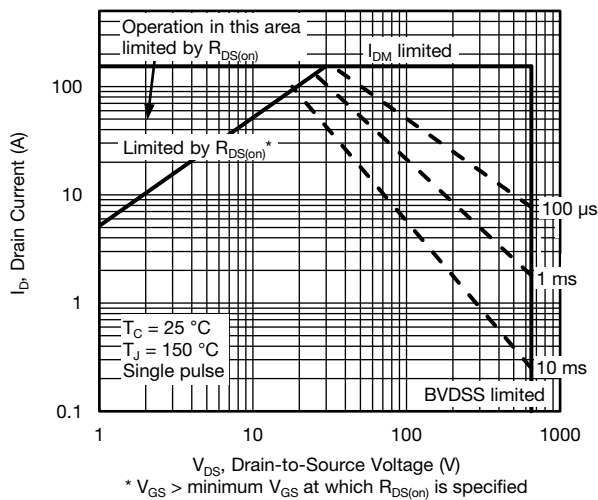


Fig. 9 - Maximum Safe Operating Area

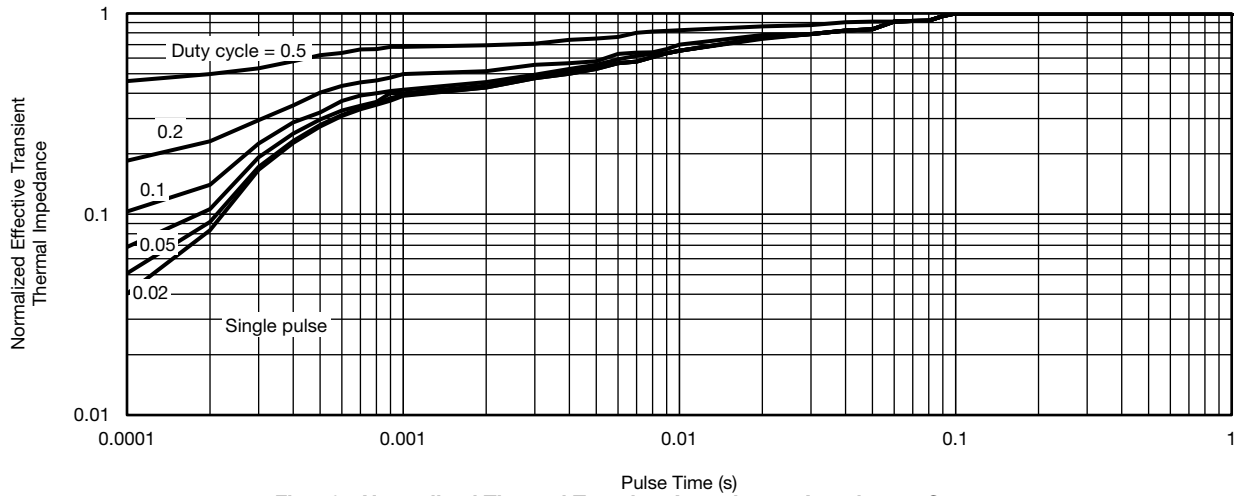


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

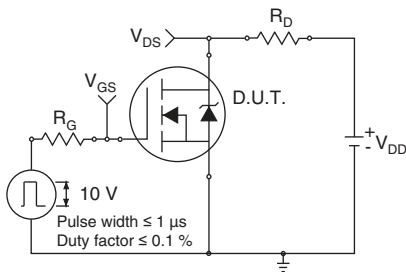


Fig. 13 - Switching Time Test Circuit

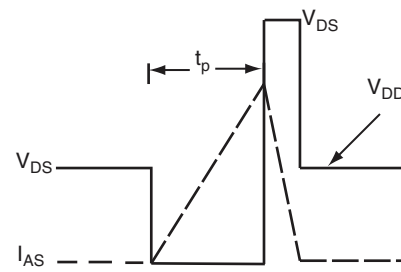


Fig. 16 - Unclamped Inductive Waveforms

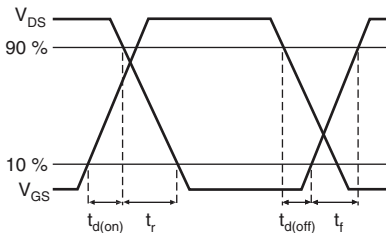


Fig. 14 - Switching Time Waveforms

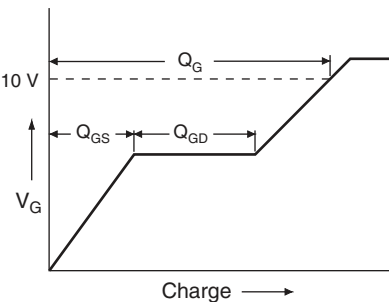


Fig. 17 - Basic Gate Charge Waveform

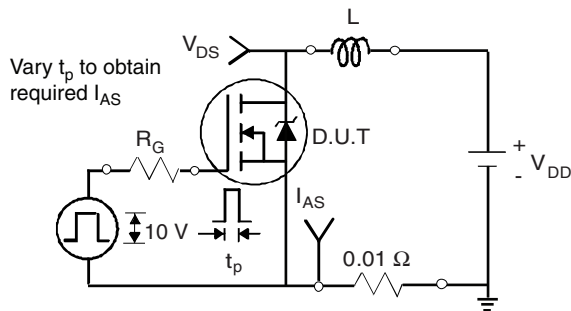


Fig. 15 - Unclamped Inductive Test Circuit

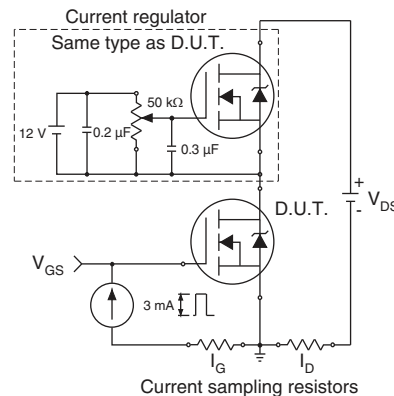
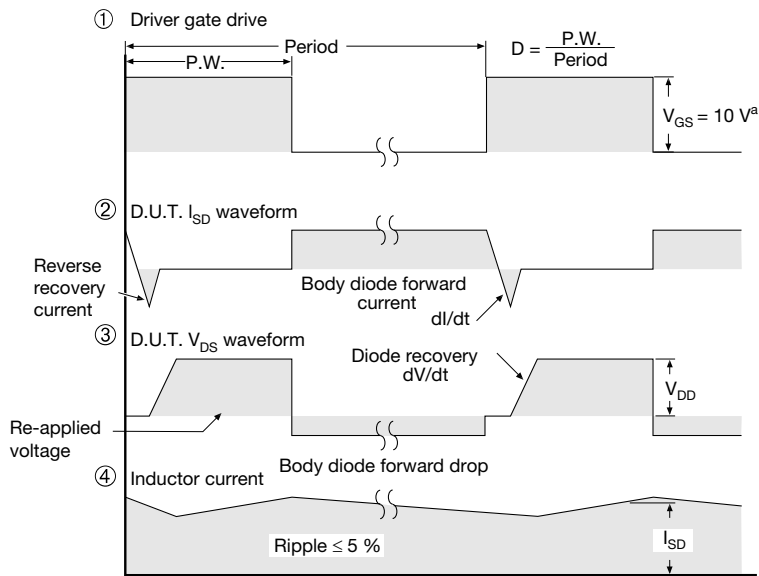
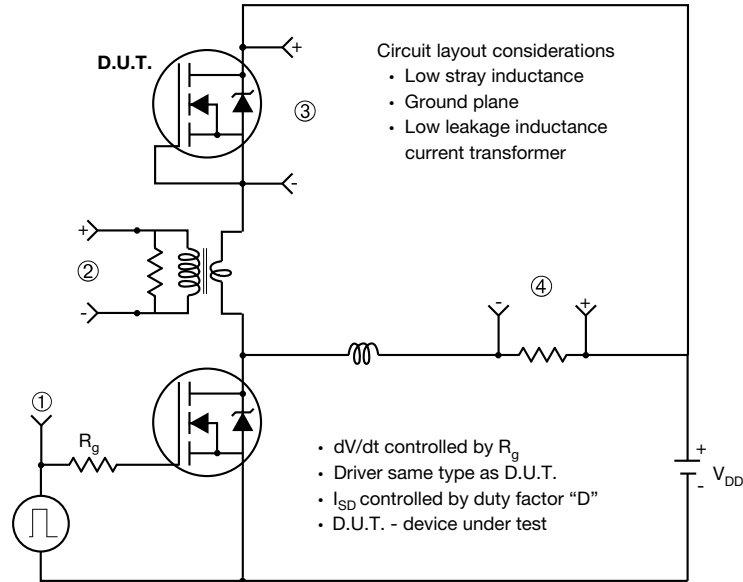


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a.  $V_{GS} = 5 V$  for logic level devices

Fig. 19 - For N-Channel

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